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STC04IE170HV

Monolithic emitter switched bipolar transistor ESBT[®] 1700 V - 4 A - 0.17 Ω

Features

V _{CS(ON)}	I _C	R _{CS(ON)}
0.7 V	4 A	0.17 Ω

- High voltage / high current cascode configuration
- Low equivalent ON resistance
- Very fast-switch: up to 150 kHz
- Squared RBSOA: up to 1700 V
- Very low C_{ISS} driven by $R_G = 47 \Omega$
- Very low turn-off cross over time

Application

■ Aux SMPS for three-phase mains

Description

The STC04IE170HV is manufactured in monolithic ESBT technology, aimed at providing the best performance in high frequency / high voltage applications. It is designed for use in gate driven based topologies.

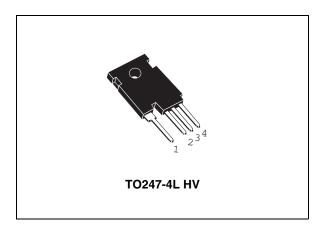


Figure 1. Internal schematic diagrams

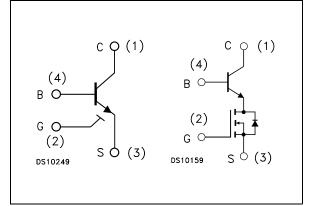


Table 1. Device summary

Order code	de Marking Package		Packing	
STC04IE170HV	C04IE170HV	TO247-4L HV	Tube	



Electrical ratings

STC04IE170HV

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CS(SS)}	Collector-source voltage ($V_{BS} = V_{GS} = 0$)	1700	V
V _{BS(OS)}	Base-source voltage ($I_C = 0$, $V_{GS} = 0$)	30	V
V _{SB(OS)}	Source-base voltage ($I_C = 0$, $V_{GS} = 0$)	17	V
V _{GS}	Gate-source voltage	± 17	V
Ι _C	Collector current	4	Α
I _{CM}	Collector peak current (t _P < 5 ms)	8	Α
Ι _Β	Base current	4	Α
I _{BM}	Base peak current (t _P < 1 ms)	8	Α
P _{tot}	Total dissipation at $T_c \le 25 \text{ °C}$	178	W
T _{stg}	Storage temperature	-40 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case	0.7	°C/W



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2 Electrical characteristics

($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

Table 4.	Electrical characteristics						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
I _{CS(SS)}	Collector cut-off current $(V_{BS} = V_{GS} = 0)$	V _{CS} = 1700 V			100	μA	
I _{BS(OS)}	Base cut-off current ($I_C = 0$, $V_{GS} = 0$)	V _{BS} = 30 V			10	μA	
I _{SB(OS)}	Source cut-off current $(I_{C} = 0, V_{GS} = 0)$	V _{SB} = 17 V			100	μA	
I _{GS(OS)}	Gate-source leakage current (V _{BS} = 0)	V _{GS} = ± 17 V			100	nA	
V _{CS(ON)}	Collector-source ON voltage	$V_{GS} = 10 V I_C = 4 A I_B = 0.8 A$ $V_{GS} = 10 V I_C = 1.5 A I_B = 0.15 A$		0.7 0.6	1.5 1.4	V V	
$h_{FE}^{(1)}$	DC current gain	$V_{CS} = 1 V V_{GS} = 10 V I_C = 4 A$ $V_{CS} = 1 V V_{GS} = 10 V I_C = 1.5 A$	4 7	5.5 11			
V _{BS(ON)}	Base-source ON voltage			1.3 0.9	1.5 1.1	V V	
V _{GS(th)}	Gate threshold voltage	$V_{BS} = V_{GS}$ $I_B = 250 \ \mu A$	2	3	4	V	
C _{iss}	Input capacitance $(V_{GS} = V_{CB} = 0)$	V _{CS} = 25 V f = 1 MHz		510		pF	
Q _{GS(tot)}	Gate-source charge (V _{CB} = 0)	V _{GS} = 10 V		3.9		nC	
t _s t _f	Inductive load Storage time Fall time	$ \begin{array}{ll} V_{GS} = 10 \ V & R_G = 47 \ \Omega \\ V_{Clamp} = 1360 \ V & t_p = 4 \ \mu s \\ I_C = 2 \ A & I_B = 0.4 \ A \end{array} $		770 10		ns ns	
t _s t _f	Inductive load Storage time Fall time			410 10		ns ns	
V _{CS(dyn)}	Collector-source dynamic voltage (0.5 µs)	$\begin{split} & V_{\text{CC}} = V_{\text{Clamp}} = 400 \; V \\ & V_{\text{GS}} = 10 \; V & I_{\text{C}} = 1.5 \; A \\ & I_{\text{B}} = 0.3 \; A & t_{\text{peak}} = 500 \; \text{ns} \\ & R_{\text{G}} = 47 \; \Omega & I_{\text{Bpeak}} = 3 \; A \; (2I_{\text{C}} \;) \end{split}$		5.36		v	
V _{CS(dyn)}	Collector-source dynamic voltage (1 µs)	$\begin{split} V_{CC} &= V_{Clamp} = 400 \ V \\ V_{GS} &= 10 \ V \qquad I_C = 1.5 \ A \\ I_B &= 0.3 \ A \qquad t_{peak} = 500 \ ns \\ R_G &= 47 \ \Omega \qquad I_{Bpeak} = 3 \ A \ (2I_C) \end{split}$		4.32		v	
V _{CSW}	Maximum collector- source voltage at turn- off without snubber	$R_{G} = 47 \Omega$ $h_{FE} = 5$ $I_{C} = 4 A$	1700			v	

Table 4. Electrical characteristics

1. Pulsed duration = 300 μ s, duty cycle \leq 1.5%.





Electrical characteristics

STC04IE170HV

2.1 **Electrical characteristics (curves)**

Figure 2. **Output characteristics**

|_B =0.8A |_B =0.6A

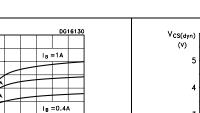
 $|_{c}(A)|$

5

3

2

0

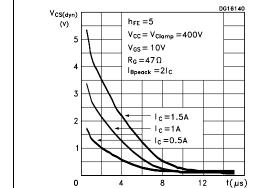


I_B =0.2A

 $V_{GS} = 10V$

0.8 V_{cs}(V)

Figure 3. **Collector-source dynamic** voltage



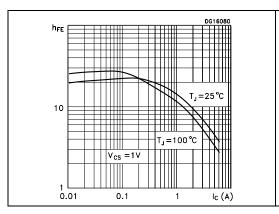


0.2

0.4

0.6

Figure 5. Gate threshold voltage vs. temperature



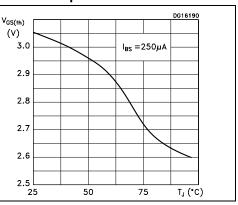
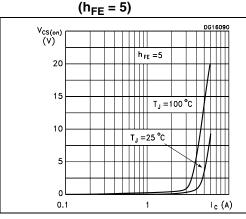


Figure 6. Collector-source ON voltage



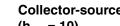
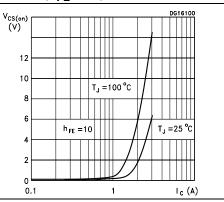


Figure 7.

Collector-source ON voltage $(h_{FE} = 10)$



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Electrical characteristics

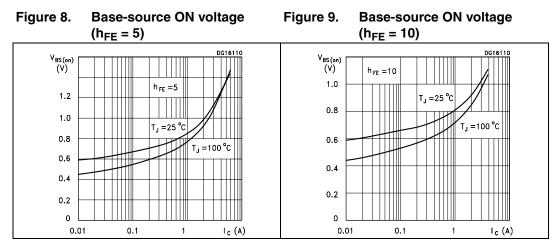


Figure 10. Inductive load switching time Figure 11. Inductive load switching time $(h_{FE} = 5)$ $(h_{FE} = 10)$

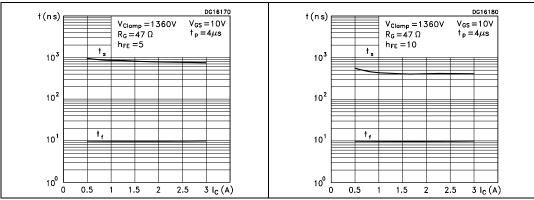
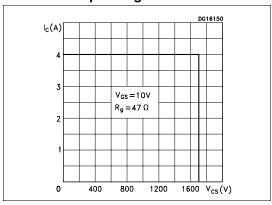


Figure 12. Reverse biased safe operating area







Package mechanical data

STC04IE170HV

3 Package mechanical data

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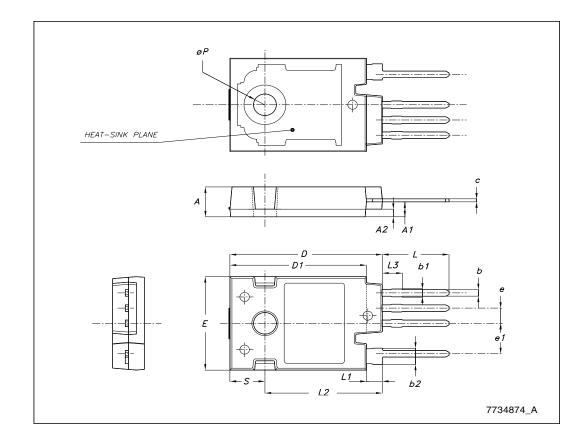
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STC04IE170HV

Package mechanical data

TO247-4L HV mechanical data

DIM		mm.	
	MIN.	ТҮР	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b1	1.10		1.50
b2	2.50		2.90
с	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e		2.54	
e1		5.08	
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	







Revision history

STC04IE170HV

4 Revision history

Table 5.Document revision history

Date	Revision	Changes	
11-Sep-2006	1	First release.	
21-Nov-2006	2	Improved application target.	
16-Jun-2009	3	Updated Figure 2 on page 4 and mechanical data.	





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